

#### 60V P-Channel Enhancement Mode MOSFET

Voltage -60 V Current -250mA

#### **Features**

- RDS(ON), VGS@-10V, ID@-500mA<4Ω
- RDS(ON), VGS@-4.5V, ID@-200mA<6Ω
- RDS(ON), VGS@-2.5V, ID@-50mA<13Ω</li>
- Advanced Trench Process Technology
- Specially Designed for Relay driver, Speed line drive, etc.
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

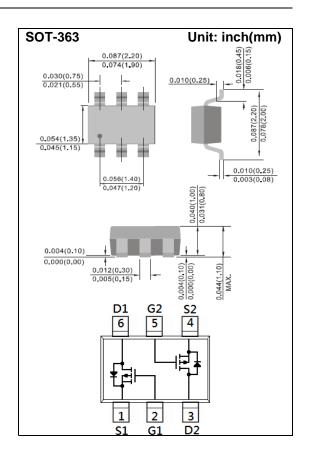
#### **Mechanical Data**

Case: SOT-363 Package

Terminals : Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0002 ounces, 0.006 grams

Marking: T39



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	-60	V
Gate-Source Voltage		V <sub>G</sub> s	<u>+</u> 20	V
Continuous Drain Current		ID	-250	mA
Pulsed Drain Current		I <sub>DM</sub>	-1000	mA
Power Dissipation	T <sub>A</sub> =25°C	_	350	mW
	Derate above 25°C	P <sub>D</sub>	2.8	mW/°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C
Typical Thermal resistance				
- Junction to Ambient (Note 3)		Reja	357	°C/W



## **Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =-250uA	-60	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1.0	-1.5	-2.5	V	
Drain-Source On-State Resistance	RDS(on)	V <sub>GS</sub> =-10V,I <sub>D</sub> =-500mA	-	2.4	4	Ω	
		V <sub>GS</sub> =-4.5V,I <sub>D</sub> =-200mA	-	2.65	6		
		V <sub>GS</sub> =-2.5V,I <sub>D</sub> =-50mA	-	4.5	13		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-48V,V <sub>GS</sub> =0V	-	-	-1	uA	
Gate-Source Leakage Current	Igss	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 4)							
Total Gate Charge	$Q_g$	\/ OF\/   400m A	-	1.1	-	nC	
Gate-Source Charge	$Q_gs$	$V_{DS}$ =-25V, $I_{D}$ =-100mA, $V_{GS}$ =-4.5V	-	0.3	-		
Gate-Drain Charge	$Q_{gd}$	VGS=-4.5 V	-	0.2	-		
Input Capacitance	Ciss	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	-	51	-	pF	
Output Capacitance	Coss	V <sub>DS</sub> =-25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	15	-		
Reverse Transfer Capacitance	Crss	I=1.0IVIMZ	-	2.2	-		
Turn-On Delay Time	td <sub>(on)</sub>		-	4.8	-		
Turn-On Rise Time	tr	V <sub>DD</sub> =-25V, I <sub>D</sub> =-100mA,	-	19	-	ns	
Turn-Off Delay Time	td <sub>(off)</sub>	V <sub>GS</sub> =-10V,	-	52	-		
Turn-Off Fall Time	tf	R <sub>G</sub> =6Ω (Note 1,2)	-	32	-		
Drain-Source Diode							
Maximum Continuous Drain-Source Diode Forward Current	ls		-	-	-250	mA	
Diode Forward Voltage	V <sub>SD</sub>	Is=-500mA, V <sub>GS</sub> =0V	-	-0.95	-1.3	٧	

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. mounted on a 1 inch square pad of copper
- 4. Guaranteed by design, not subject to production testing



#### **TYPICAL CHARACTERISTIC CURVES**

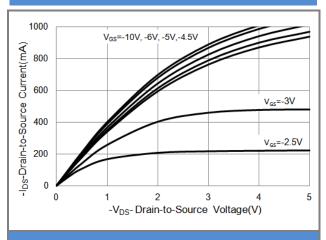
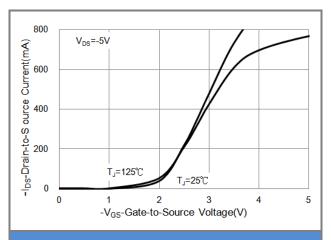


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

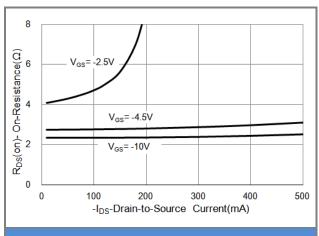


Fig.3 On-Resistance vs. Drain Current

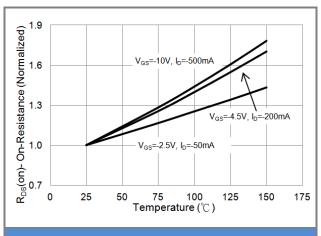
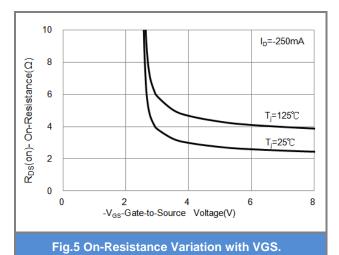
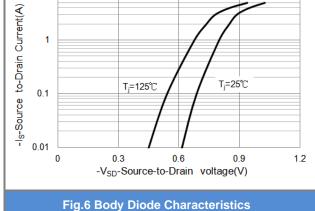


Fig.4 On-Resistance vs. Junction temperature





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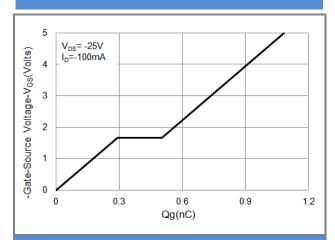


Fig.7 Gate-Charge Characteristics

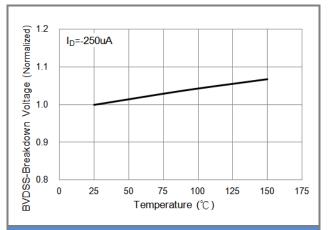


Fig.8 Breakdown Voltage Variation vs. Temperature

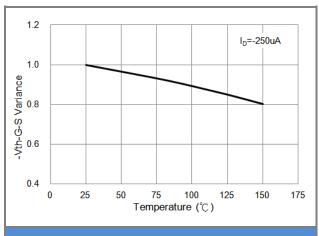


Fig.9 Threshold Voltage Variation with Temperature.

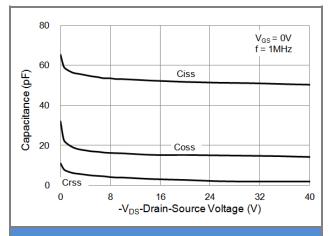


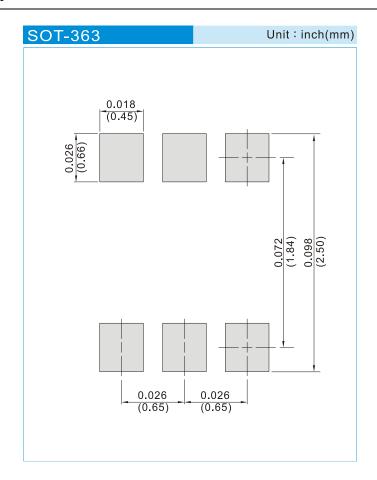
Fig.10 Capacitance vs. Drain-Source Voltage.



# **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking
PJT7839	SOT-363	3K pcs / 7" reel	T39
PJT7839	SOT-363	10K pcs / 13" reel	T39

# **Mounting Pad Layout**





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